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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	68K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f205rbt6tr

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If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The TIM1 and TIM8 counters can be frozen in debug mode. Many of the advanced-control timer features are shared with those of the standard TIMx timers which have the same architecture. The advanced-control timer can therefore work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

3.20.2 General-purpose timers (TIMx)

There are ten synchronizable general-purpose timers embedded in the STM32F20x devices (see [Table 5](#) for differences).

TIM2, TIM3, TIM4, TIM5

The STM32F20x include 4 full-featured general-purpose timers. TIM2 and TIM5 are 32-bit timers, and TIM3 and TIM4 are 16-bit timers. The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input capture/output compare/PWMs on the largest packages.

The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.

The counters of TIM2, TIM3, TIM4, TIM5 can be frozen in debug mode. Any of these general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 4 hall-effect sensors.

TIM10, TIM11 and TIM9

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10 and TIM11 feature one independent channel, whereas TIM9 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

TIM12, TIM13 and TIM14

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM13 and TIM14 feature one independent channel, whereas TIM12 has two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers.

They can also be used as simple time bases.

3.20.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger and waveform generation. They can also be used as a generic 16-bit time base.

The interface allows data transfer at up to 48 MHz in 8-bit mode, and is compliant with the SD Memory Card Specification Version 2.0.

The SDIO Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

In addition to SD/SDIO/MMC, this interface is fully compliant with the CE-ATA digital protocol Rev1.1.

3.26 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

Peripheral available only on the STM32F207xx devices.

The STM32F207xx devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for ethernet LAN communications through an industry-standard medium-independent interface (MII) or a reduced medium-independent interface (RMII). The STM32F207xx requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). the PHY is connected to the STM32F207xx MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) or 50 MHz (RMII) output from the STM32F207xx.

The STM32F207xx includes the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors (see the STM32F20x and STM32F21x reference manual for details)
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes, that is 4 Kbytes in total
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

3.27 Controller area network (CAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOs with 3 stages and 28 shared scalable filter banks (all of them can be used even if one

3.30 Audio PLL (PLL12S)

The devices feature an additional dedicated PLL for audio I²S application. It allows to achieve error-free I²S sampling clock accuracy without compromising on the CPU performance, while using USB peripherals.

The PLL12S configuration can be modified to manage an I²S sample rate change without disabling the main PLL (PLL) used for CPU, USB and Ethernet interfaces.

The audio PLL can be programmed with very low error to obtain sampling rates ranging from 8 kHz to 192 kHz.

In addition to the audio PLL, a master clock input pin can be used to synchronize the I2S flow with an external PLL (or Codec output).

3.31 Digital camera interface (DCMI)

The camera interface is not available in STM32F205xx devices.

STM32F207xx products embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain up to 27 Mbyte/s at 27 MHz or 48 Mbyte/s at 48 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw Bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

3.32 True random number generator (RNG)

All STM32F2xxx products embed a true RNG that delivers 32-bit random numbers produced by an integrated analog circuit.

3.33 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O alternate function configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

To provide fast I/O handling, the GPIOs are on the fast AHB1 bus with a clock up to 120 MHz that leads to a maximum I/O toggling speed of 60 MHz.

Table 8. STM32F20x pin and ball definitions (continued)

Pins						Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
-	-	56	78	97	P14	PD9	I/O	FT	-	FSMC_D14, USART3_RX, EVENTOUT	-
-	-	57	79	98	N15	PD10	I/O	FT	-	FSMC_D15, USART3_CK, EVENTOUT	-
-	-	58	80	99	N14	PD11	I/O	FT	-	FSMC_A16, USART3_CTS, EVENTOUT	-
-	-	59	81	100	N13	PD12	I/O	FT	-	FSMC_A17, TIM4_CH1, USART3_RTS, EVENTOUT	-
-	-	60	82	101	M15	PD13	I/O	FT	-	FSMC_A18, TIM4_CH2, EVENTOUT	-
-	-	-	83	102	-	V _{SS}	S	-	-	-	-
-	-	-	84	103	J13	V _{DD}	S	-	-	-	-
-	-	61	85	104	M14	PD14	I/O	FT	-	FSMC_D0, TIM4_CH3, EVENTOUT	-
-	-	62	86	105	L14	PD15	I/O	FT	-	FSMC_D1, TIM4_CH4, EVENTOUT	-
-	-	-	87	106	L15	PG2	I/O	FT	-	FSMC_A12, EVENTOUT	-
-	-	-	88	107	K15	PG3	I/O	FT	-	FSMC_A13, EVENTOUT	-
-	-	-	89	108	K14	PG4	I/O	FT	-	FSMC_A14, EVENTOUT	-
-	-	-	90	109	K13	PG5	I/O	FT	-	FSMC_A15, EVENTOUT	-
-	-	-	91	110	J15	PG6	I/O	FT	-	FSMC_INT2, EVENTOUT	-
-	-	-	92	111	J14	PG7	I/O	FT	-	FSMC_INT3, USART6_CK, EVENTOUT	-
-	-	-	93	112	H14	PG8	I/O	FT	-	USART6_RTS, ETH_PPS_OUT, EVENTOUT	-
-	-	-	94	113	G12	V _{SS}	S	-	-	-	-
-	-	-	95	114	H13	V _{DD}	S	-	-	-	-
37	G2	63	96	115	H15	PC6	I/O	FT	-	I2S2_MCK, TIM8_CH1, SDIO_D6, USART6_TX, DCMI_D0, TIM3_CH1, EVENTOUT	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\Sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$ (for the $1.8\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\Sigma$).

6.1.3 Typical curves

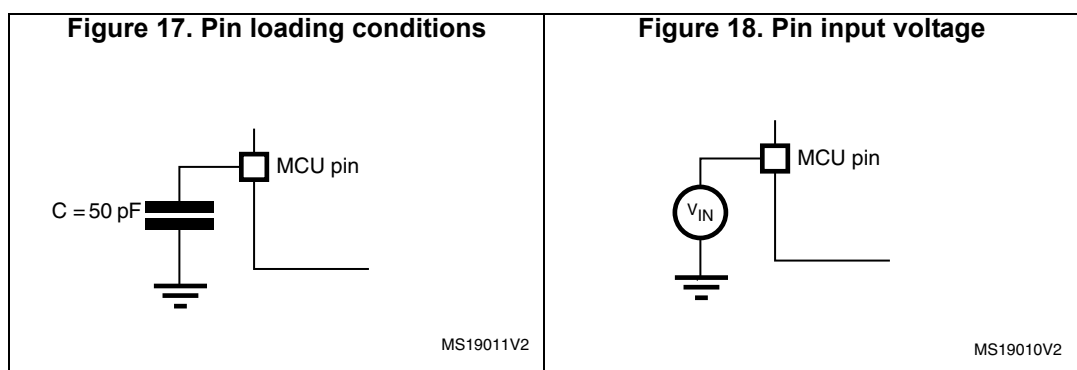
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 17](#).

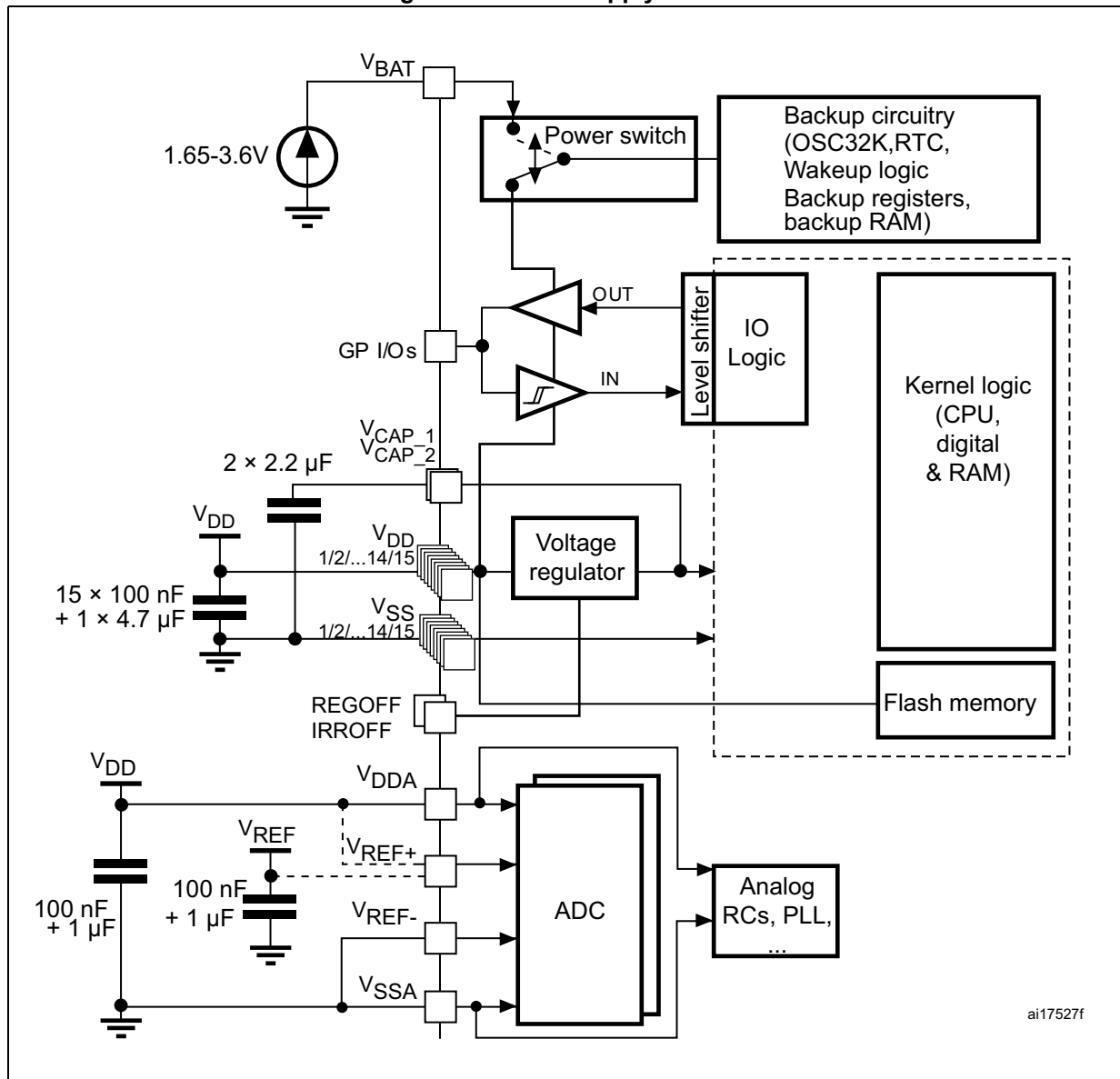
6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 18](#).



6.1.6 Power supply scheme

Figure 19. Power supply scheme



1. Each power supply pair must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.
2. To connect REGOFF and IRROFF pins, refer to [Section 3.16: Voltage regulator](#).
3. The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
4. The 4.7 μF ceramic capacitor must be connected to one of the VDD pin.

Caution: Each power supply pair (V_{DD}/V_{SS} , V_{DDA}/V_{SSA} ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB, to ensure good device operation. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect device operation.

Table 19. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	V
		Rising edge	2.53	2.59	2.63	V
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	V
		Rising edge	2.85	2.92	2.97	V
$V_{BORhyst}^{(1)}$	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPO}^{(1)(2)}$	Reset temporization	-	0.5	1.5	3.0	ms
$I_{RUSH}^{(1)}$	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
$E_{RUSH}^{(1)}$	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	$V_{DD} = 1.8\text{ V}$, $T_A = 105\text{ }^{\circ}\text{C}$, $I_{RUSH} = 171\text{ mA}$ for $31\text{ }\mu\text{s}$	-	-	5.4	μC

1. Guaranteed by design, not tested in production.

2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 20: Current consumption measurement scheme](#).

All Run mode current consumption measurements given in this section are performed using CoreMark[®] code.

Table 26. Peripheral current consumption (continued)

Peripheral ⁽¹⁾		Typical consumption at 25 °C	Unit
APB2	SDIO	0.69	mA
	TIM1	1.06	
	TIM8	1.03	
	TIM9	0.58	
	TIM10	0.37	
	TIM11	0.39	
	ADC1 ⁽⁴⁾	2.13	
	ADC2 ⁽⁴⁾	2.04	
	ADC3 ⁽⁴⁾	2.12	
	SPI1	1.20	
	USART1	0.38	
	USART6	0.37	

1. External clock is 25 MHz (HSE oscillator with 25 MHz crystal) and PLL is on.
2. EN1 bit is set in DAC_CR register.
3. EN2 bit is set in DAC_CR register.
4. $f_{ADC} = f_{PCLK2}/2$, ADON bit set in ADC_CR2 register.

6.3.7 Wakeup time from low-power mode

The wakeup times given in [Table 27](#) is measured on a wakeup phase with a 16 MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

Table 27. Low-power mode wakeup timings

Symbol	Parameter	Min ⁽¹⁾	Typ ⁽¹⁾	Max ⁽¹⁾	Unit
$t_{WUSLEEP}^{(2)}$	Wakeup from Sleep mode	-	1	-	μs
$t_{WUSTOP}^{(2)}$	Wakeup from Stop mode (regulator in Run mode)	-	13	-	μs
	Wakeup from Stop mode (regulator in low-power mode)	-	17	40	
	Wakeup from Stop mode (regulator in low-power mode and Flash memory in Deep power down mode)	-	110	-	
$t_{WUSTDBY}^{(2)(3)}$	Wakeup from Standby mode	260	375	480	μs

1. Guaranteed by characterization results, not tested in production.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.
3. $t_{WUSTDBY}$ minimum and maximum values are given at 105 °C and -45 °C, respectively.

Table 39. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
t_{prog}	Double word programming	$T_A = 0$ to $+40$ °C $V_{DD} = 3.3$ V $V_{PP} = 8.5$ V	-	16	100 ⁽²⁾	μ s
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	6.9	-	s
V_{prog}	Programming voltage	-	2.7	-	3.6	V
V_{PP}	V_{PP} voltage range	-	7	-	9	V
I_{PP}	Minimum current sunk on the V_{PP} pin	-	10	-	-	mA
$t_{VPP}^{(3)}$	Cumulative time during which V_{PP} is applied	-	-	-	1	hour

1. Guaranteed by design, not tested in production.
2. The maximum programming time is measured after 100K erase operations.
3. V_{PP} should only be connected during programming/erasing.

Table 40. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min ⁽¹⁾	
N_{END}	Endurance	$T_A = -40$ to $+85$ °C (6 suffix versions) $T_A = -40$ to $+105$ °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle ⁽²⁾ at $T_A = 85$ °C	30	Years
		1 kcycle ⁽²⁾ at $T_A = 105$ °C	10	
		10 kcycles ⁽²⁾ at $T_A = 55$ °C	20	

1. Guaranteed by characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC[®] code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 42. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{CPU}]	Unit
				25/120 MHz	
S _{EMI}	Peak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running with ART enabled, peripheral clock disabled	0.1 to 30 MHz	25	dBμV
			30 to 130 MHz		
			130 MHz to 1GHz		
			SAE EMI Level	4	-
		V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running with ART enabled, PLL spread spectrum enabled, peripheral clock disabled	0.1 to 30 MHz	28	dBμV
			30 to 130 MHz	26	
			130 MHz to 1GHz	22	
			SAE EMI level	4	-

6.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

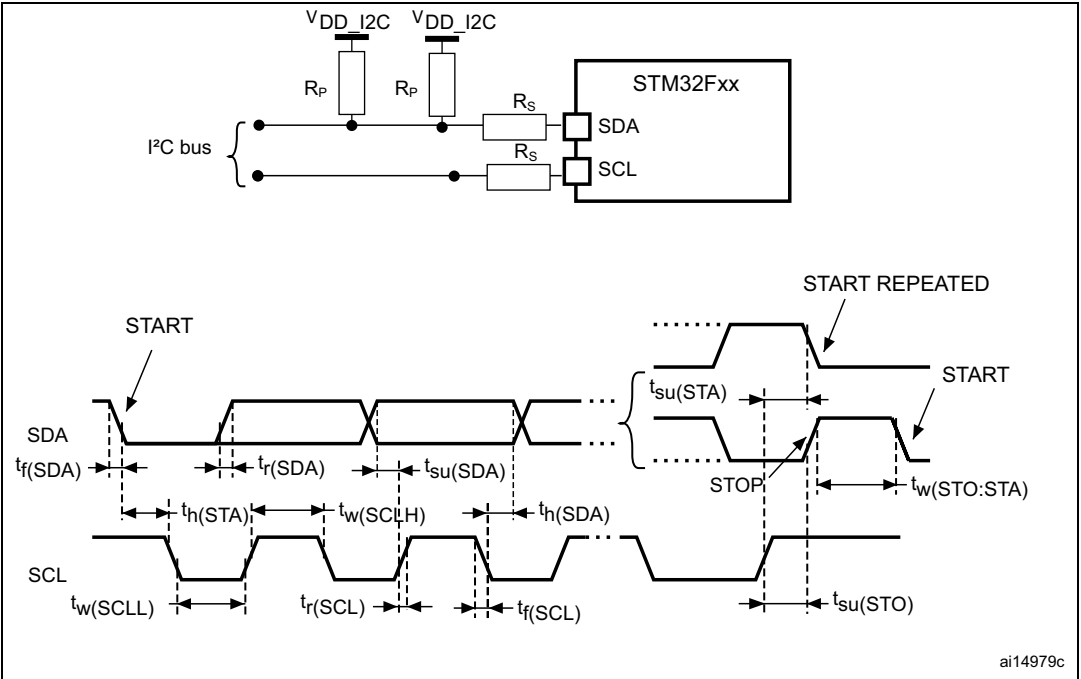
Table 43. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C conforming to JESD22-A114	2	2000 ⁽²⁾	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C conforming to JESD22-C101	II	500	

1. Guaranteed by characterization results, not tested in production.

2. On V_{BAT} pin, V_{ESD(HBM)} is limited to 1000 V.

Figure 41. I²C bus AC waveforms and measurement circuit



1. R_S = series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I²C bus power supply.

Table 53. SCL frequency ($f_{PCLK1} = 30 \text{ MHz}$, $V_{DD} = 3.3 \text{ V}$)⁽¹⁾⁽²⁾

f_{SCL} (kHz)	I2C_CCR value
	$R_P = 4.7 \text{ k}\Omega$
400	0x8019
300	0x8021
200	0x8032
100	0x0096
50	0x012C
20	0x02EE

1. R_P = External pull-up resistance, f_{SCL} = I²C speed,
2. For speeds around 200 kHz, the tolerance on the achieved speed is of $\pm 5\%$. For other speed ranges, the tolerance on the achieved speed $\pm 2\%$. These variations depend on the accuracy of the external components used to design the application.

USB OTG FS characteristics

The USB OTG interface is USB-IF certified (Full-Speed). This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 56. USB OTG FS startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB OTG FS transceiver startup time	1	μs

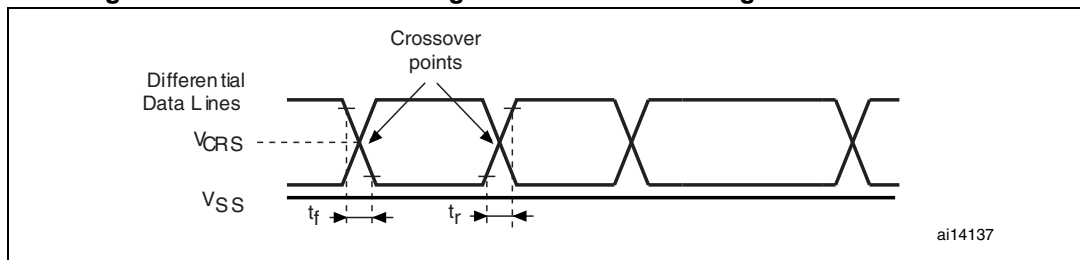
1. Guaranteed by design, not tested in production.

Table 57. USB OTG FS DC electrical characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
Input levels	V_{DD}	USB OTG FS operating voltage	3.0 ⁽²⁾	-	3.6	V
	$V_{\text{DI}}^{(3)}$	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	-	-	V
	$V_{\text{CM}}^{(3)}$	Differential common mode range	Includes V_{DI} range	-	2.5	
	$V_{\text{SE}}^{(3)}$	Single ended receiver threshold		-	2.0	
Output levels	V_{OL}	Static output level low	R_{L} of 1.5 k Ω to 3.6 V ⁽⁴⁾	-	0.3	V
	V_{OH}	Static output level high	R_{L} of 15 k Ω to $V_{\text{SS}}^{(4)}$	-	3.6	
R_{PD}	PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	$V_{\text{IN}} = V_{\text{DD}}$	17	21	24	k Ω
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0	
R_{PU}	PA12, PB15 (USB_FS_DP, USB_HS_DP)	$V_{\text{IN}} = V_{\text{SS}}$	1.5	1.8	2.1	
	PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	$V_{\text{IN}} = V_{\text{SS}}$	0.25	0.37	0.55	

1. All the voltages are measured from the local ground potential.
2. The STM32F205xx and STM32F207xx USB OTG FS functionality is ensured down to 2.7 V but not the full USB OTG FS electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design, not tested in production.
4. R_{L} is the load connected on the USB OTG FS drivers

Figure 47. USB OTG FS timings: definition of data signal rise and fall time

Table 58. USB OTG FS electrical characteristics⁽¹⁾

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_f	Fall time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_{rfm}	Rise/fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

1. Guaranteed by design, not tested in production.
2. Measured from 10% to 90% of the data signal. For more detailed informations, refer to USB Specification - Chapter 7 (version 2.0).

USB HS characteristics

Table 59 shows the USB HS operating voltage.

Table 59. USB HS DC electrical characteristics

Symbol	Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
Input level V_{DD}	USB OTG HS operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 60. Clock timing parameters

Parameter ⁽¹⁾		Symbol	Min	Nominal	Max	Unit
Frequency (first transition)	8-bit $\pm 10\%$	F_{START_8BIT}	54	60	66	MHz
Frequency (steady state)	$\pm 500 \text{ ppm}$	F_{STEADY}	59.97	60	60.03	MHz
Duty cycle (first transition)	8-bit $\pm 10\%$	D_{START_8BIT}	40	50	60	%
Duty cycle (steady state)	$\pm 500 \text{ ppm}$	D_{STEADY}	49.975	50	50.025	%
Time to reach the steady state frequency and duty cycle after the first transition		T_{STEADY}	-	-	1.4	ms
Clock startup time after the de-assertion of SuspendM	Peripheral	T_{START_DEV}	-	-	5.6	ms
	Host	T_{START_HOST}	-	-	-	
PHY preparation time after the first transition of the input clock		T_{PREP}	-	-	-	μs

1. Guaranteed by design, not tested in production.

Figure 48. ULPI timing diagram

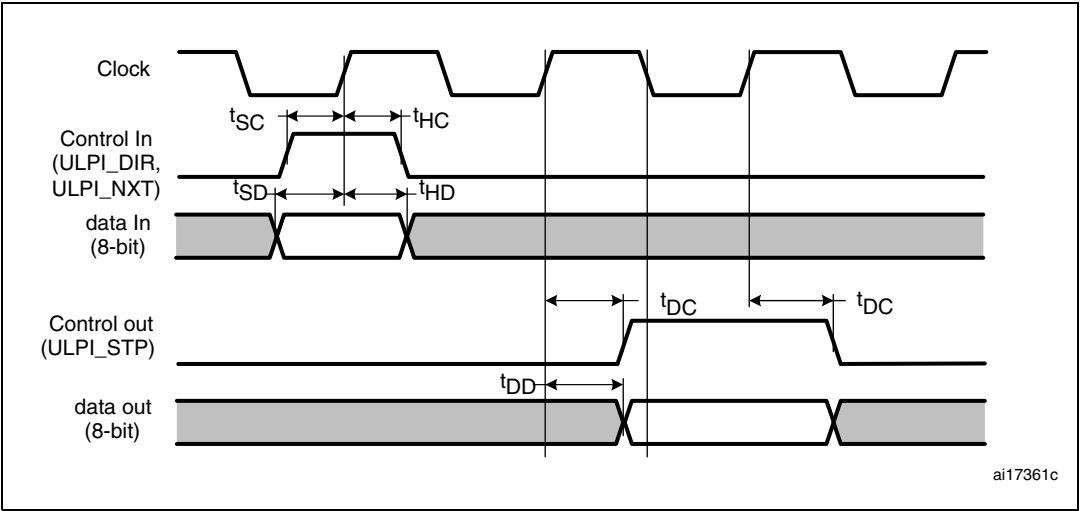


Table 61. ULPI timing

Symbol	Parameter	Value ⁽¹⁾		Unit
		Min	Max	
t_{SC}	Control in (ULPI_DIR) setup time	-	2.0	ns
	Control in (ULPI_NXT) setup time	-	1.5	
t_{HC}	Control in (ULPI_DIR, ULPI_NXT) hold time	0	-	
t_{SD}	Data in setup time	-	2.0	
t_{HD}	Data in hold time	0	-	
t_{DC}	Control out (ULPI_STP) setup time and hold time	-	9.2	
t_{DD}	Data out available from clock rising edge	-	10.7	

1. $V_{DD} = 2.7\text{ V}$ to 3.6 V and $T_A = -40$ to $85\text{ }^{\circ}\text{C}$.

Ethernet characteristics

Table 62 shows the Ethernet operating voltage.

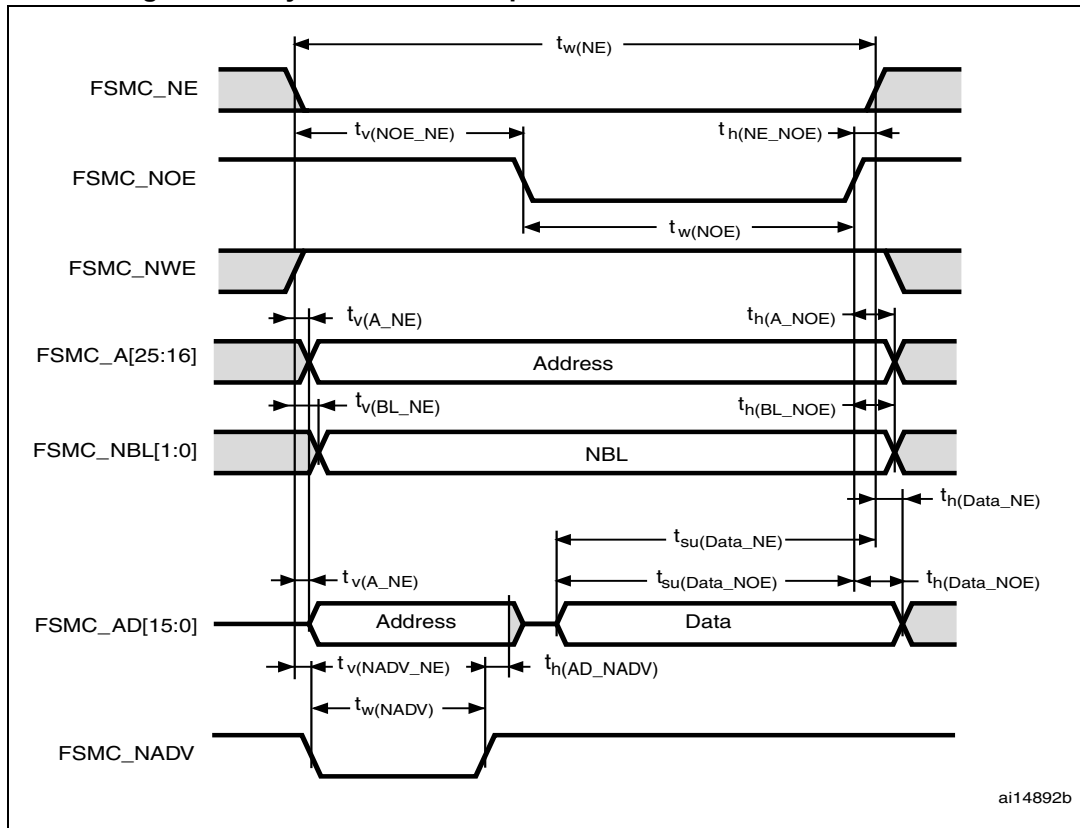
Table 62. Ethernet DC electrical characteristics

Symbol		Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
Input level	V_{DD}	Ethernet operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 63 gives the list of Ethernet MAC signals for the SMI (station management interface) and Figure 49 shows the corresponding timing diagram.

Figure 59. Asynchronous multiplexed PSRAM/NOR read waveforms

Table 74. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_w(NE)$	FSMC_NE low time	$3T_{HCLK}-1$	$3T_{HCLK}+1$	ns
$t_v(NOE_NE)$	FSMC_NEx low to FSMC_NOE low	$2T_{HCLK}$	$2T_{HCLK}+0.5$	ns
$t_w(NOE)$	FSMC_NOE low time	$T_{HCLK}-1$	$T_{HCLK}+1$	ns
$t_h(NE_NOE)$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_v(A_NE)$	FSMC_NEx low to FSMC_A valid	-	2	ns
$t_v(NADV_NE)$	FSMC_NEx low to FSMC_NADV low	1	2.5	ns
$t_w(NADV)$	FSMC_NADV low time	$T_{HCLK}-1.5$	T_{HCLK}	ns
$t_h(AD_NADV)$	FSMC_AD(adress) valid hold time after FSMC_NADV high	T_{HCLK}	-	ns
$t_h(A_NOE)$	Address hold time after FSMC_NOE high	T_{HCLK}	-	ns
$t_h(BL_NOE)$	FSMC_BL time after FSMC_NOE high	0	-	ns
$t_v(BL_NE)$	FSMC_NEx low to FSMC_BL valid	-	1	ns
$t_{su}(Data_NE)$	Data to FSMC_NEx high setup time	$T_{HCLK}+2$	-	ns
$t_{su}(Data_NOE)$	Data to FSMC_NOE high setup time	$T_{HCLK}+3$	-	ns

Figure 61. Synchronous multiplexed NOR/PSRAM read timings

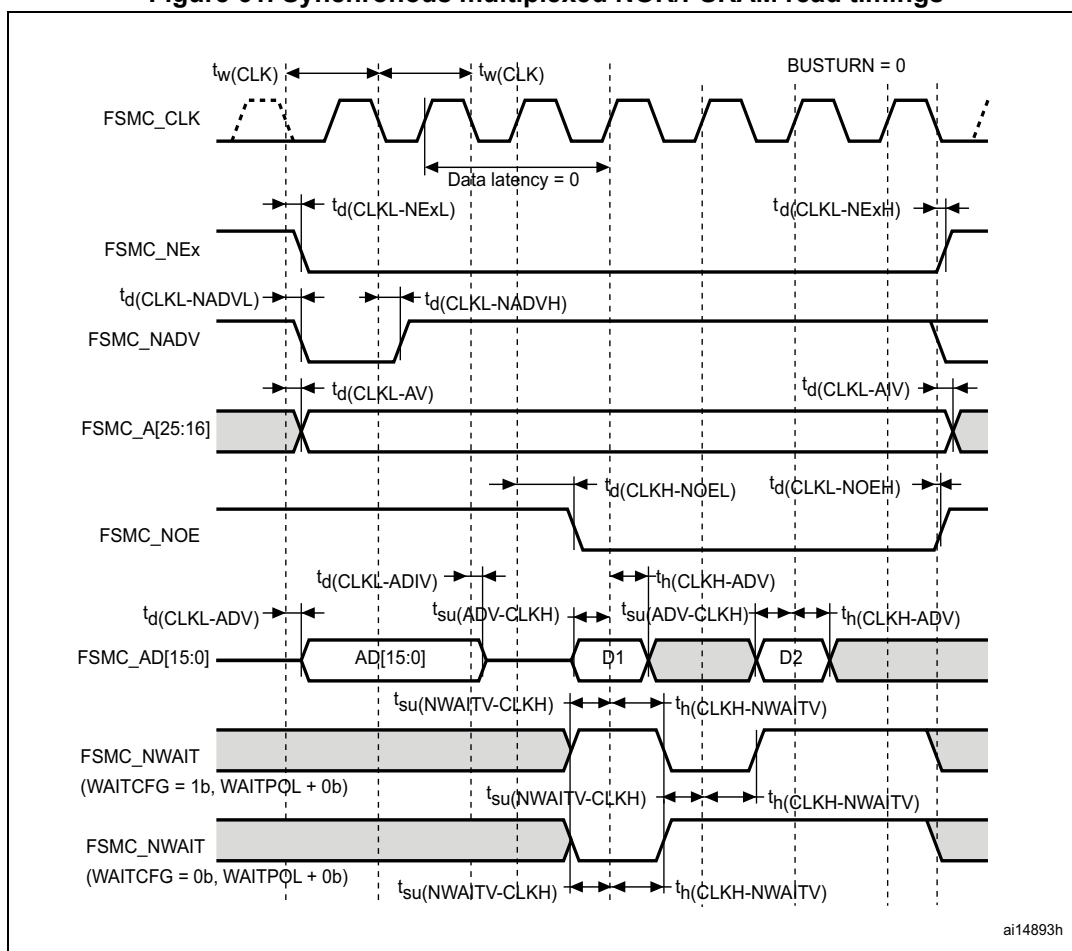


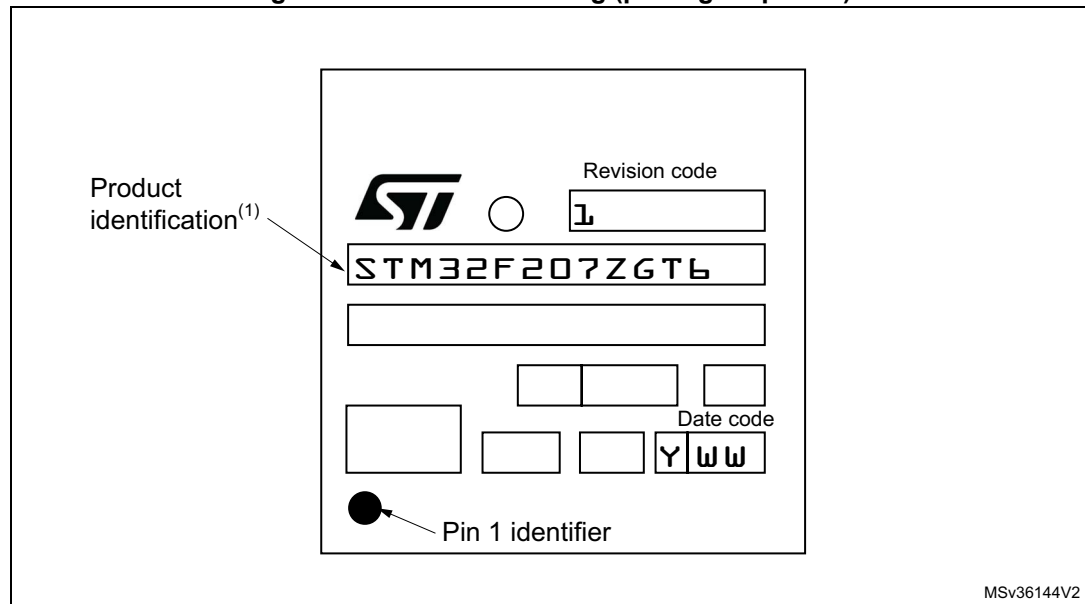
Table 76. Synchronous multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2T_{HCLK}$	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	0	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x= 0...2)	1	-	ns
$t_{d(CLKL-NADV_L)}$	FSMC_CLK low to FSMC_NADV low	-	1.5	ns
$t_{d(CLKL-NADV_H)}$	FSMC_CLK low to FSMC_NADV high	2.5	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x=16...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x=16...25)	0	-	ns
$t_{d(CLKH-NOEL)}$	FSMC_CLK high to FSMC_NOE low	-	1	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	1	-	ns
$t_{d(CLKL-ADV)}$	FSMC_CLK low to FSMC_AD[15:0] valid	-	3	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns

Device marking

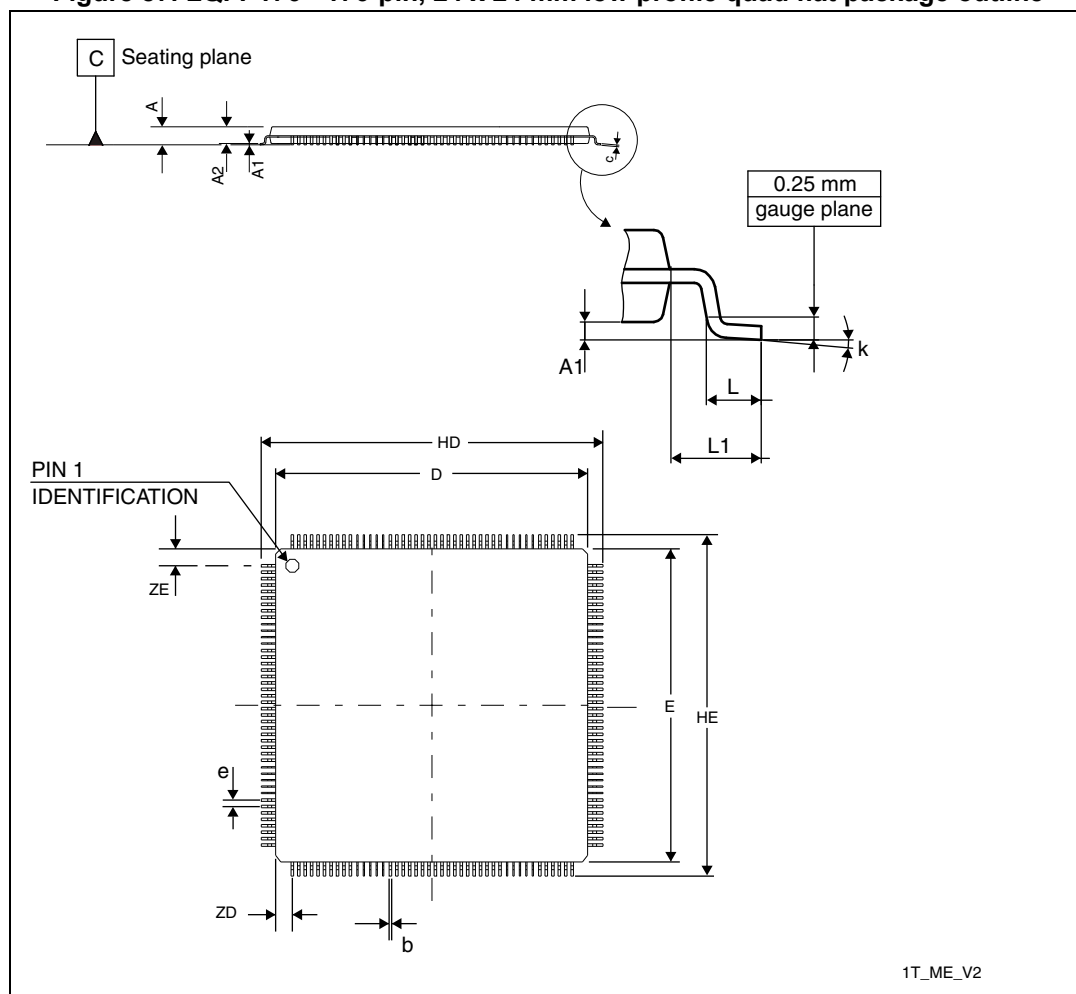
Figure 86 gives an example of topside marking orientation versus Pin 1 identifier location.

Figure 86. LQFP144 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Figure 87. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package outline



1. Drawing is not to scale.

Table 92. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package mechanical data

Symbol	Dimensions					
	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0571
b	0.170	-	0.270	0.0067	-	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488

Table 97. Document revision history (continued)

Date	Revision	Changes
04-Nov-2013	11	<p>In the whole document, updated notes related to WLCSP64+2 usage with IRROFF set to V_{DD}. Updated Section 3.14: Power supply schemes, Section 3.15: Power supply supervisor, Section 3.16.1: Regulator ON and Section 3.16.2: Regulator OFF. Added Section 3.16.3: Regulator ON/OFF and internal reset ON/OFF availability. Added note related to WLCSP64+2 package.</p> <p>Restructured RTC features and added reference clock detection in Section 3.17: Real-time clock (RTC), backup SRAM and backup registers.</p> <p>Added note indicating the package view below Figure 10: STM32F20x LQFP64 pinout, Figure 12: STM32F20x LQFP100 pinout, Figure 13: STM32F20x LQFP144 pinout, and Figure 14: STM32F20x LQFP176 pinout.</p> <p>Added Table 7: Legend/abbreviations used in the pinout table. Table 8: STM32F20x pin and ball definitions: content reformatted; removed indexes on V_{SS} and V_{DD}; updated PA4, PA5, PA6, PC4, BOOT0; replaced DCMI_12 by DCMI_D12, TIM8_CHIN by TIM8_CH1N, ETH_MII_RX_D0 by ETH_MII_RXD0, ETH_MII_RX_D1 by ETH_MII_RXD1, ETH_RMII_RX_D0 by ETH_RMII_RXD0, ETH_RMII_RX_D1 by ETH_RMII_RXD1, and RMII_CRS_DV by ETH_RMII_CRS_DV.</p> <p>Table 10: Alternate function mapping: replaced FSMC_BLN1 by FSMC_NBL1, added EVENTOUT as AF15 alternated function for PC13, PC14, PC15, PH0, PH1, and PI8.</p> <p>Updated Figure 17: Pin loading conditions and Figure 18: Pin input voltage.</p> <p>Added V_{IN} in Table 14: General operating conditions.</p> <p>Removed note applying to $V_{POR/PDR}$ minimum value in Table 19: Embedded reset and power control block characteristics.</p> <p>Updated notes related to C_{L1} and C_{L2} in Section : Low-speed external clock generated from a crystal/ceramic resonator.</p> <p>Updated conditions in Table 41: EMS characteristics. Updated Table 42: EMI characteristics. Updated V_{IL}, V_{IH} and V_{Hys} in Table 46: I/O static characteristics. Added Section : Output driving current and updated Figure 39: I/O AC characteristics definition.</p> <p>Updated $V_{IL(NRST)}$ and $V_{IH(NRST)}$ in Table 49: NRST pin characteristics, updated Figure 39: I/O AC characteristics definition.</p> <p>Removed tests conditions in Section : I2C interface characteristics.</p> <p>Updated Table 52: I2C characteristics and Figure 41: I2C bus AC waveforms and measurement circuit.</p> <p>Updated I_{VREF+} and I_{VDDA} in Table 66: ADC characteristics. Updated Offset comments in Table 68: DAC characteristics.</p> <p>Updated minimum $t_{h(CLKH-DV)}$ value in Table 78: Synchronous non-multiplexed NOR/PSRAM read timings.</p>